

Silicon NPN Power Transistors

2SC1569

DESCRIPTION

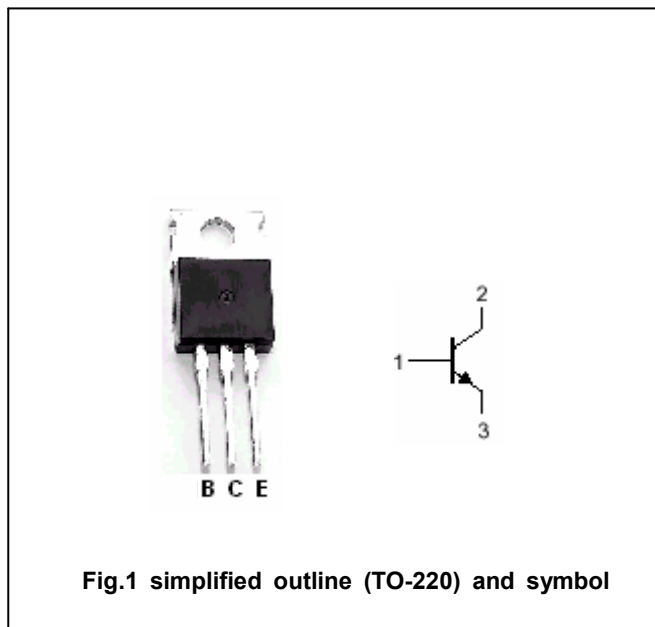
- With TO-220 package
- High breakdown voltage
- High transition frequency

APPLICATIONS

- For color TV chroma output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		0.2	A
P_C	Collector power dissipation	$T_a=25^\circ\text{C}$	1.5	W
		$T_C=25^\circ\text{C}$	12.5	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

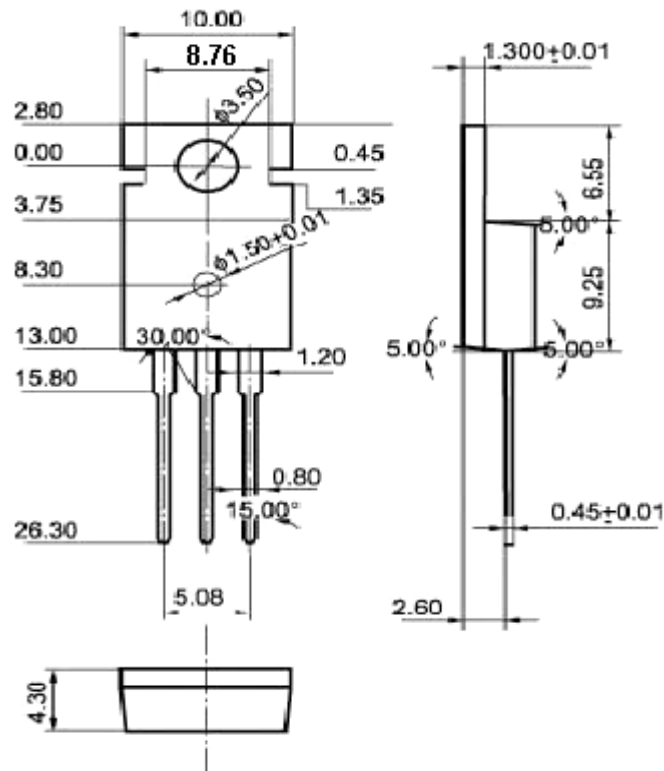
Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=10\mu A ; I_E=0$	300			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=1mA ; I_B=0$	300			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10\mu A ; I_C=0$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=100mA ; I_B=20mA$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=100mA ; I_B=20mA$			1.2	V
I_{CBO}	Collector cut-off current	$V_{CB}=100V ; I_E=0$			1.0	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			1.0	μA
h_{FE}	DC current gain	$I_C=50mA ; V_{CE}=10V$	40		170	
C_{OB}	Output capacitance	$I_E=0 ; V_{CB}=10V ; f=1MHz$		65		pF
f_T	Transition frequency	$I_C=30mA ; V_{CE}=10V$	40			MHz

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PACKAGE OUTLINE

Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)